

SD103AWS...SD103CWS-HAF

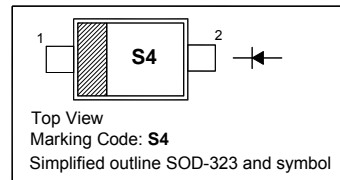
Surface Mount Schottky Barrier Diodes

Features

- Low Forward Voltage
- Halogen and Antimony Free(HAF), RoHS compliant

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	SD103AWS	40
		SD103BWS	30
		SD103CWS	20
Reverse Voltage	V_R	SD103AWS	40
		SD103BWS	30
		SD103CWS	20
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$	I_{FSM}	2	A
Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	SD103AWS	40	-	-
		SD103BWS	30	-	-
		SD103CWS	20	-	-
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$	I_R	SD103AWS	-	-	5
		SD103BWS	-	-	5
		SD103CWS	-	-	5
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	-	-	0.37	V
		-	-	0.6	
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	-	50	-	pF
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	10	-	ns

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
 ISO 9001 : 2008 Certificate No. 50114012
 OHSAS 18001 : 2007 Certificate No. 05131506008
 IECQ QC 080000 Certificate No. ESH100074002

Dated: 25/04/2015 Rev: 01

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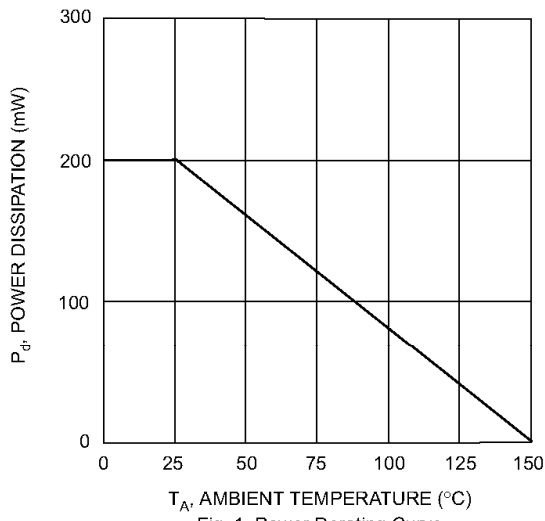


Fig. 1 Power Derating Curve

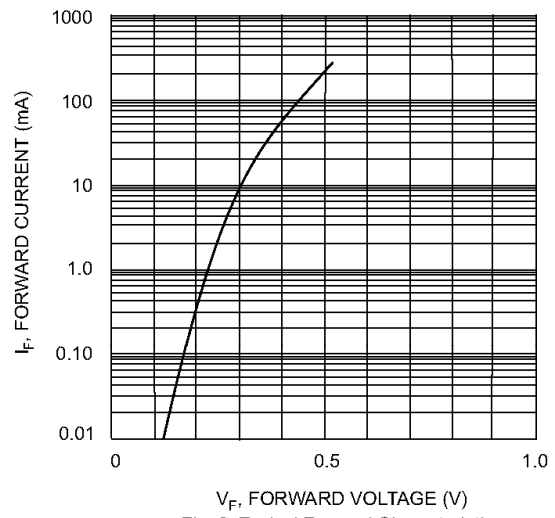


Fig. 2 Typical Forward Characteristics

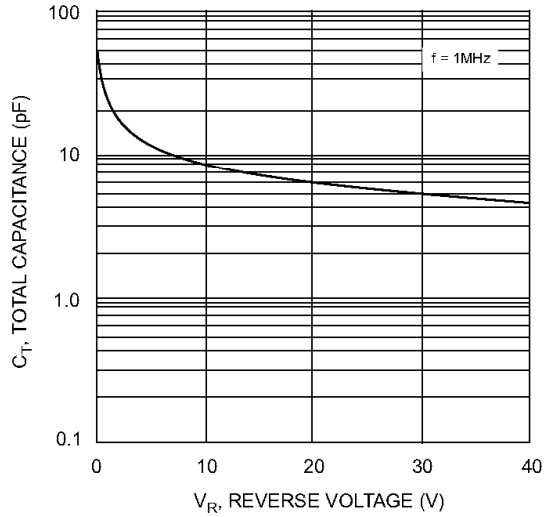


Fig. 3 Total Capacitance vs Reverse Voltage

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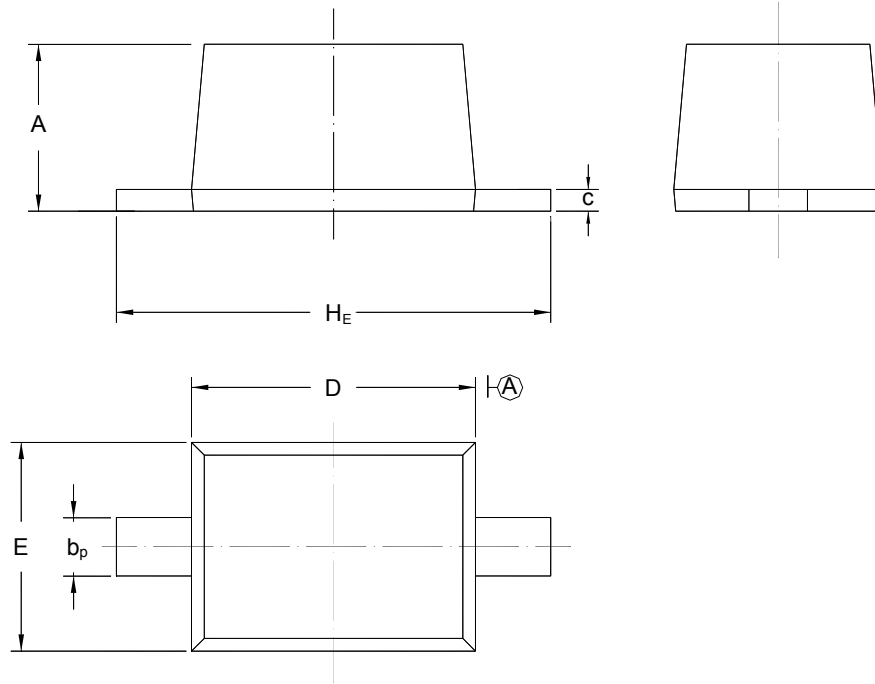


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30

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